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FDH50N50 / FDA50N50 N-Channel UniFETTM MOSFET 500 V, 48 A, 105 mΩ

Features

- + $R_{DS(on)}$ = 89 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 24 A
- Low Gate Charge (Typ. 105 nC)
- Low C_{rss} (Typ. 45 pF)
- 100% Avalanche Tested
- Improved dv/dt Capability

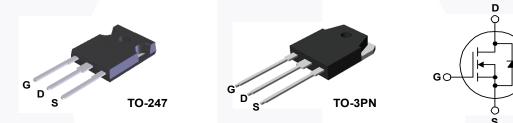
Applications

- Lighting
- Uninterruptible Power Supply
- AC-DC Power Supply

May 2014

Description

UniFETTM MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.



Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter Drain-Source Voltage		FDH50N50_F133 / FDA50N50	Unit V
V _{DSS}			500	
ID	Drain Current	- Continuous (T _C = 25°C) - Continuous (T _C = 100°C)	48 30.8	A A
I _{DM}	Drain Current	- Pulsed (Note 1)	192	А
V _{GSS}	Gate-Source voltage	±20	V	
E _{AS}	Single Pulsed Avalanche Energy (Note 2)		1868	mJ
I _{AR}	Avalanche Current (Note 1)		48	А
E _{AR}	Repetitive Avalanche Energy (Note 1)		62.5	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	20	V/ns
P _D	Power Dissipation	(T _C = 25°C) - Derate Above 25°C	625 5	W W/∘C
T _{J,} T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C
TL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		300	°C

Thermal Characteristics

Symbol	Parameter	FDH50N50_F133 / FDA50N50	Unit
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction-to-Case, Max.	0.2	°C/W
R_{\thetaJA}	Thermal Resistance, Junction-to-Ambient, Max.	40	

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Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDH50N50_F133	FDH50N50	TO-247	Tube	N/A	N/A	30 units
FDA50N50	FDA50N50	TO-3PN	Tube	N/A	N/A	30 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Off Charac	teristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, \text{ I}_{D} = 250 \mu\text{A}$	500			V
ΔBV_{DSS} / ΔT_{J}	Breakdown Voltage Temperature Coefficient	I_D = 250 µA, Referenced to 25°C		0.5		V/∘C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 500 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = 400 \text{ V}, T_{C} = 125^{\circ}\text{C}$			25 250	μΑ μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 20 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -20 V, V _{DS} = 0 V			-100	nA
On Charac	teristics					
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	3.0		5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 24 A		0.089	0.105	Ω
9 _{FS}	Forward Transconductance	V _{DS} = 40 V, I _D = 48 A		20		S
Dynamic C	Characteristics					
C _{iss}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V,		4979	6460	pF
C _{oss}	Output Capacitance	f = 1 MHz		760	1000	pF
C _{rss}	Reverse Transfer Capacitance			50	65	pF
C _{oss}	Output Capacitance	V_{DS} = 400 V, V_{GS} = 0 V, f = 1 MHz		161		pF
Coss(eff.)	Effective Output Capacitance	V_{DS} = 0 V to 400 V, V_{GS} = 0 V		342		pF
Switching	Characteristics					
t _{d(on)}	Turn-On Delay Time	V _{DD} = 250 V, I _D = 48 A,		105	220	ns
t _r	Turn-On Rise Time	V_{GS} = 10 V, R_{G} = 25 Ω		360	730	ns
t _{d(off)}	Turn-Off Delay Time		-	225	460	ns
t _f	Turn-Off Fall Time	(Note 4)		230	470	ns
Qg	Total Gate Charge	V _{DS} = 400 V, I _D = 48 A V _{GS} = 10 V		105	137	nC
Q _{gs}	Gate-Source Charge			33		nC
Q _{gd}	Gate-Drain Charge	(Note 4)		45		nC
Drain-Sou	rce Diode Characteristics and Maximur	n Ratings				
I _S	Maximum Continuous Drain-Source Diode Forward Current				48	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				192	А
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 48 A			1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 48 A,		580		ns
Q _{rr}	Reverse Recovery Charge	dI _F /dt =100 A/μs		10		μC

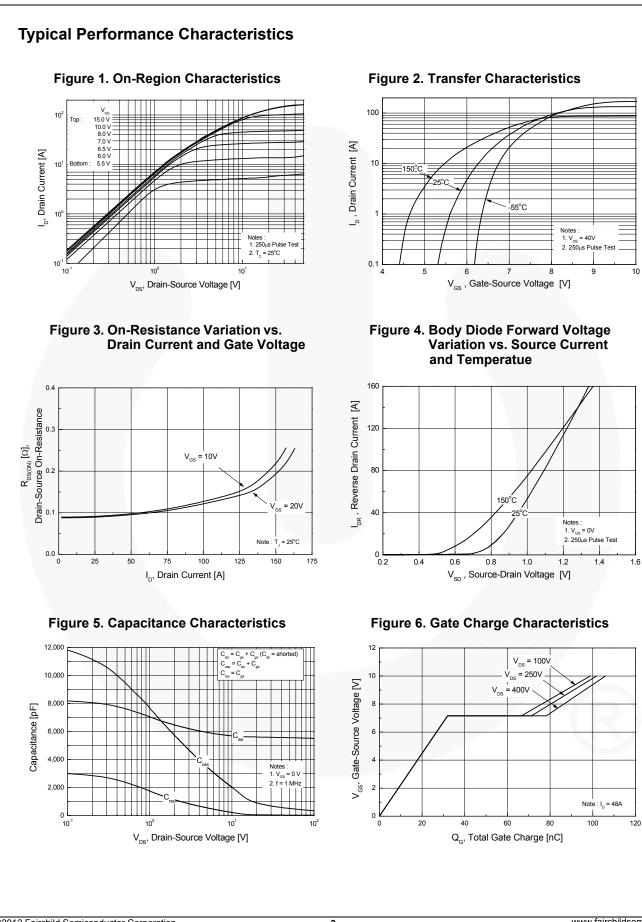
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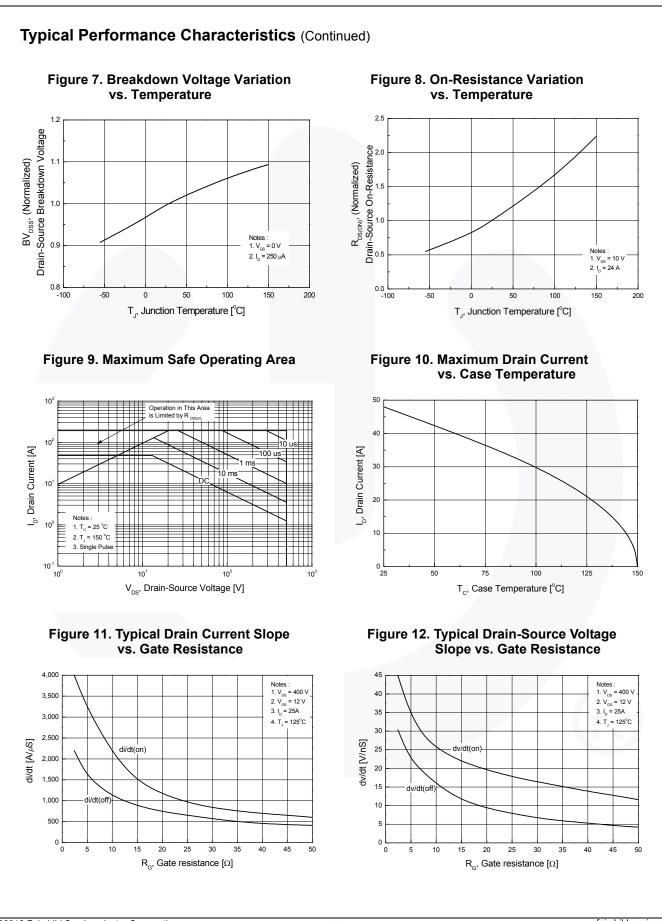
1. Repetitive rating: pulse-width limited by maximum junction temperature.

2. L = 1.46 mH, I_{AS} = 48 A, V_{DD} = 50 V, R_G = 25 $\Omega,$ starting T_J = 25°C.

3. I_{SD} \leq 48 A, di/dt \leq 200 A/µs, V_{DD} \leq BV_{DSS}, starting T_J = 25°C.

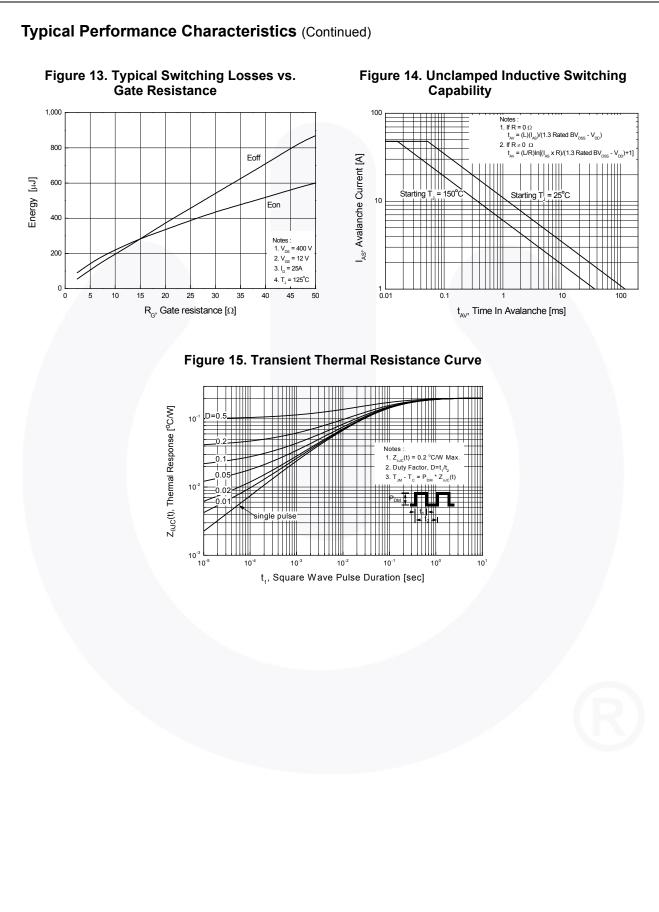
4. Essentially independent of operating temperature typical characteristics.



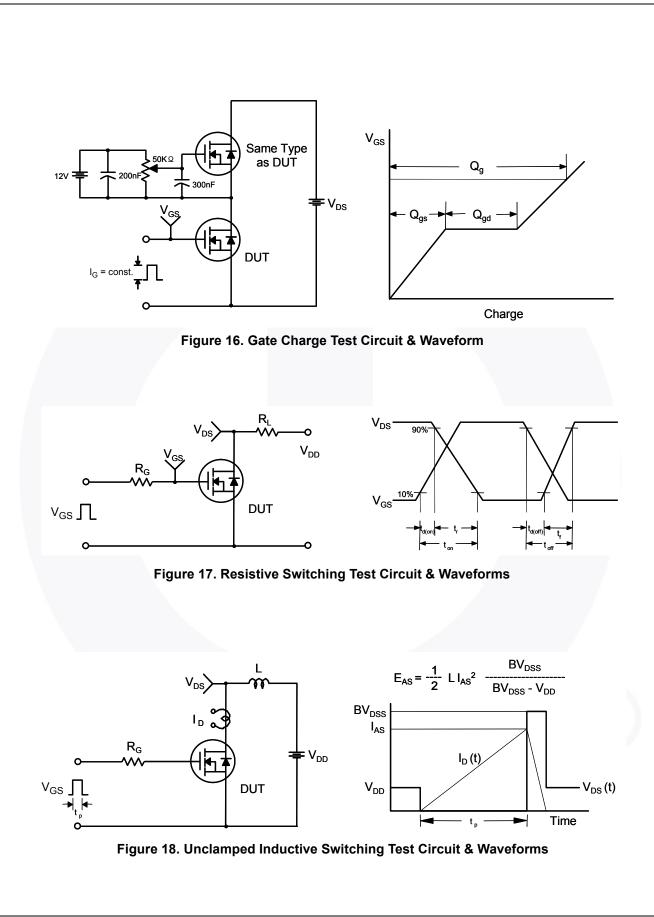


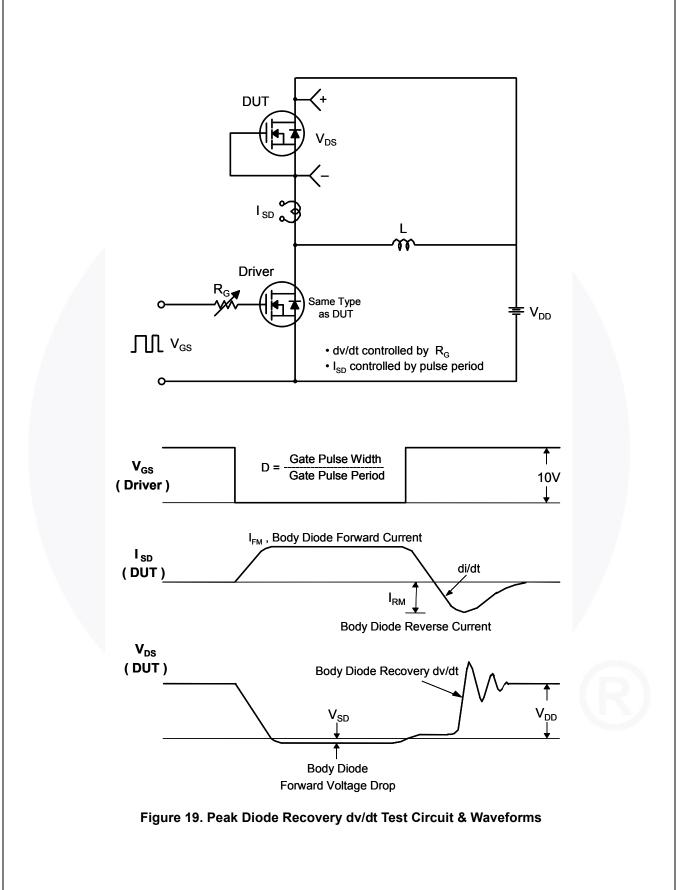
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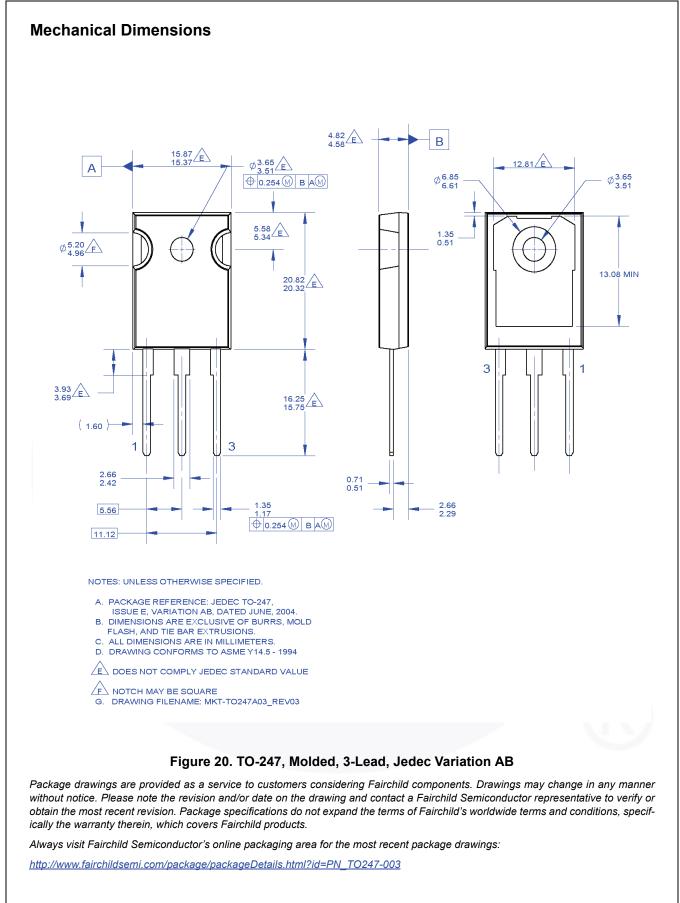
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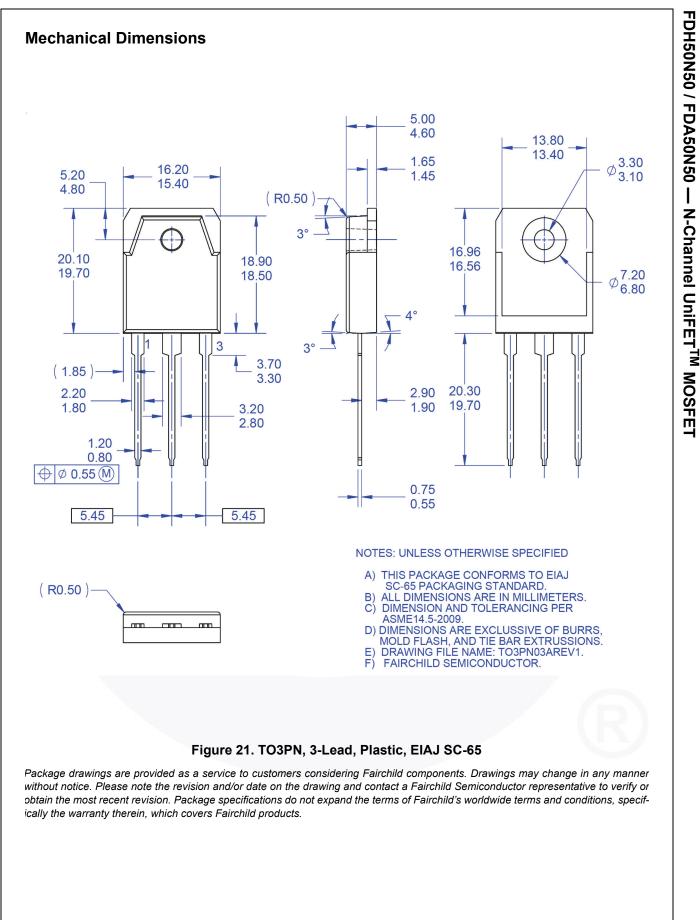


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